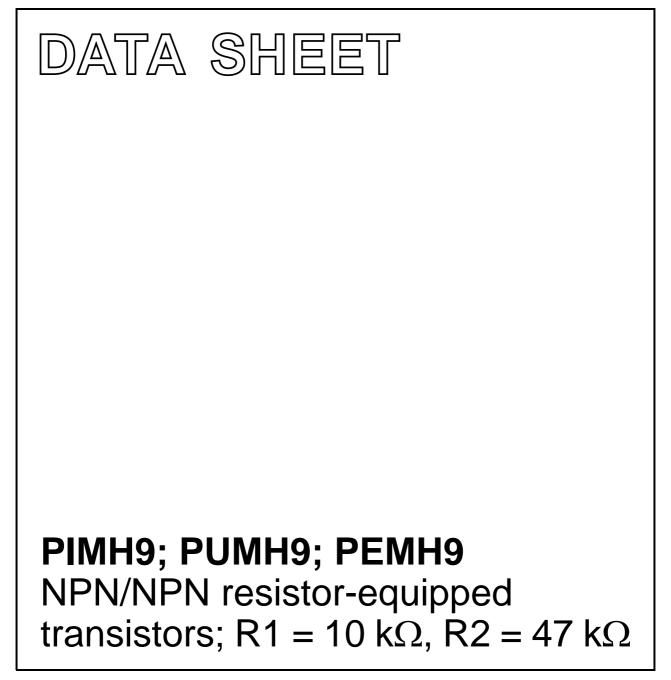
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2003 Sep 15 2004 Apr 14



PIMH9; PUMH9; PEMH9

FEATURES

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	-	50	V
lo	output current (DC)	-	100	mA
TR1	NPN	-	-	-
TR2	NPN	-	-	-
R1	bias resistor	10	-	kΩ
R2	bias resistor	47	-	kΩ

DESCRIPTION

NPN/NPN resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	PNP/PNP	NPN/PNP	
	PHILIPS	EIAJ		COMPLEMENT	COMPLEMENT	
PEMH9	SOT666	-	H9	PEMB9	PEMD9	
PIMH9	SOT457	SC-74	H9	-	-	
PUMH9	SOT363	SC-88	H*9 ⁽¹⁾	PUMB9	PUMD9	

Note

1. * = p: Made in Hong Kong.

* = t: Made in Malaysia.

* = W: Made in China.

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

	SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
TYPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	DESCRIPTION		
PEMH9		1	emitter TR1		
PIMH9		2	base TR1		
PUMH9		3	collector TR2		
		4	emitter TR2		
		5	base TR2		
		6	collectorTR1		
	Top view MHC049				

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ORDERING INFORMATION

		PACKAGE			
TYPE NUMBER NAME		DESCRIPTION	VERSION		
PEMH9	_	plastic surface mounted package; 6 leads	SOT666		
PIMH9	PIMH9 – plastic surface mounted package; 6 leads		SOT457		
PUMH9	_	plastic surface mounted package; 6 leads	SOT363		

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transis	tor				
V _{CBO}	collector-base voltage	open emitter	_	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	10	V
Vi	input voltage				
	positive		-	+40	V
	negative		_	-10	V
lo	output current		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363	note 1	_	200	mW
	SOT457	note 1	_	300	mW
	SOT666	notes 1 and 2	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C
Per device		·	·		
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363	note 1	-	300	mW
	SOT457	note 1	_	600	mW
	SOT666	notes 1 and 2	_	300	mW

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

2. Reflow soldering is the only recommended soldering method.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	tor			
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$		
	SOT363	note 1	625	K/W
	SOT457	note 1	417	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R _{th(j-a)}	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$		
	SOT363	note 1	416	K/W
	SOT457	note 1	208	K/W
	SOT666	notes 1 and 2	416	K/W

Notes

1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.

2. Reflow soldering is the only recommended soldering method.

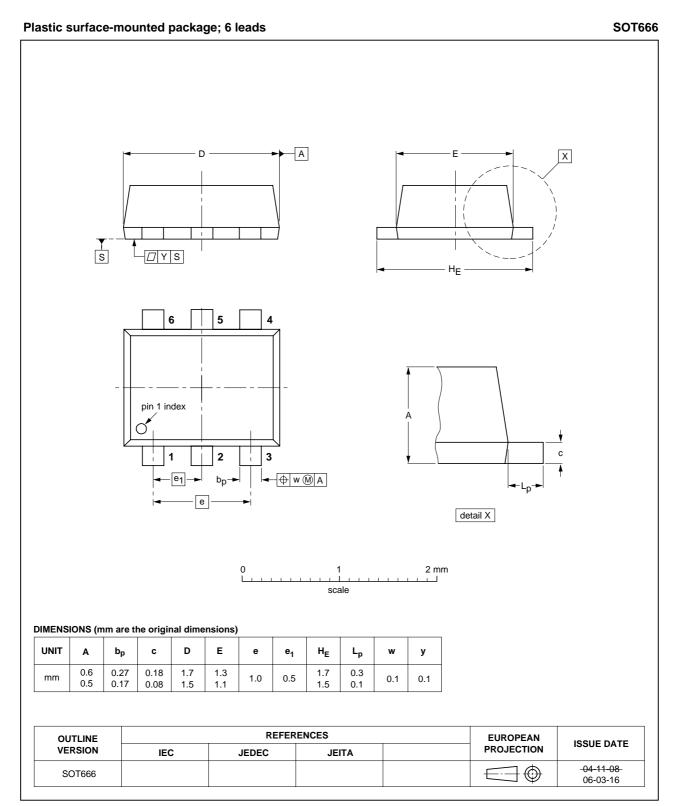
CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

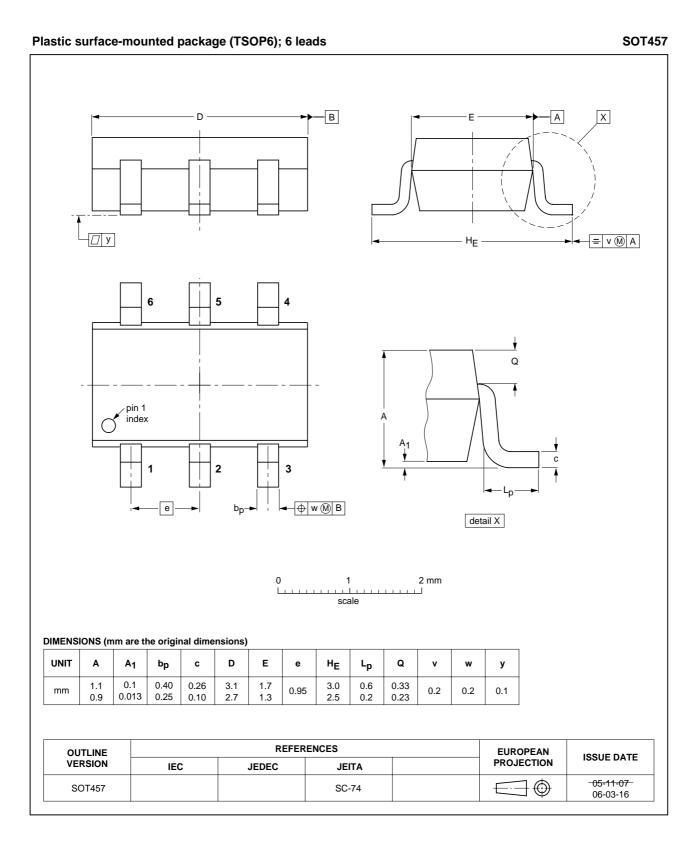
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	_	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0 A	_	-	1	μA
		$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \text{ T}_{j} = 150 ^{\circ}\text{C}$	-	_	50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	_	150	μA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	100	_	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 5 mA; I _B = 0.25 mA	_	_	100	mV
V _{i(off)}	input-off voltage	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 100 \mu\text{A}$	-	0.7	0.5	V
V _{i(on)}	input-on voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 1 \text{ mA}$	1.4	0.8	_	V
R1	input resistor		7	10	13	kΩ
R2 R1	resistor ratio		3.7	4.7	5.7	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A};$ f = 1 MHz	-	_	2.5	pF

PIMH9; PUMH9; PEMH9

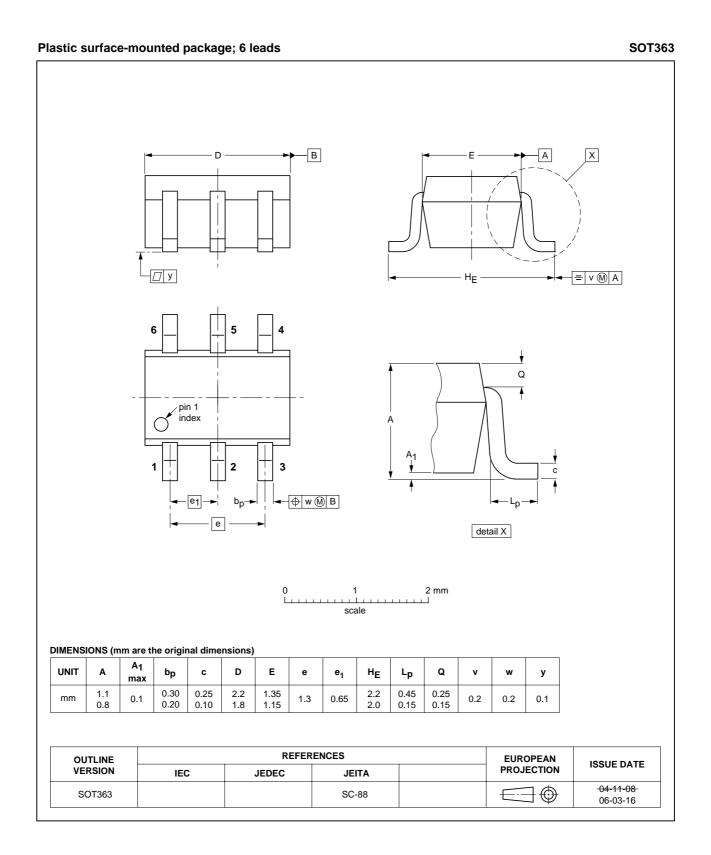
PACKAGE OUTLINES



PIMH9; PUMH9; PEMH9



PIMH9; PUMH9; PEMH9



PIMH9; PUMH9; PEMH9

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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